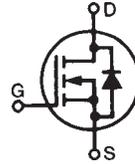


TrenchMV™ Power MOSFET

IXTA130N10T IXTP130N10T

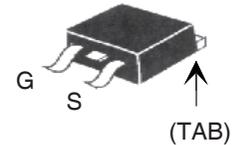
$V_{DSS} = 100V$
 $I_{D25} = 130A$
 $R_{DS(on)} \leq 9.1m\Omega$

N-Channel Enhancement Mode
Avalanche Rated

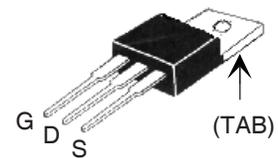


Symbol	Test Conditions	Maximum Ratings	
V_{DSS}	$T_J = 25^\circ C$ to $175^\circ C$	100	V
V_{DGR}	$T_J = 25^\circ C$ to $175^\circ C$, $R_{GS} = 1M\Omega$	100	V
V_{GSM}	Transient	± 30	V
I_{D25}	$T_C = 25^\circ C$	130	A
I_{LRMS}	Lead Current Limit, RMS	75	A
I_{DM}	$T_C = 25^\circ C$, pulse width limited by T_{JM}	350	A
I_A	$T_C = 25^\circ C$	65	A
E_{AS}	$T_C = 25^\circ C$	500	mJ
P_D	$T_C = 25^\circ C$	360	W
T_J		-55 ... +175	$^\circ C$
T_{JM}		175	$^\circ C$
T_{stg}		-55 ... +175	$^\circ C$
T_L	1.6mm (0.062 in.) from case for 10s	300	$^\circ C$
T_{SOLD}	Plastic body for 10 seconds	260	$^\circ C$
M_d	Mounting torque (TO-220)	1.13 / 10	Nm/lb.in.
Weight	TO-220	3.0	g
	TO-263	2.5	g

TO-263 (IXTA)



TO-220 (IXTP)



G = Gate D = Drain
S = Source TAB = Drain

Features

- Ultra-low On Resistance
- Unclamped Inductive Switching (UIS) rated
- Low package inductance
 - easy to drive and to protect
- 175 $^\circ C$ Operating Temperature

Advantages

- Easy to mount
- Space savings
- High power density

Applications

- Automotive
 - Motor Drives
 - 42V Power Bus
 - ABS Systems
- DC/DC Converters and Off-line UPS
- Primary Switch for 24V and 48V Systems
- Distributed Power Architectures and VRMs
- Electronic Valve Train Systems
- High Current Switching Applications
- High Voltage Synchronous Rectifier

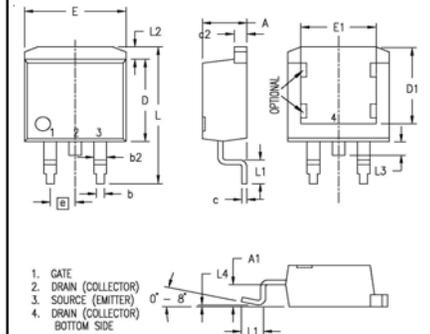
Symbol	Test Conditions ($T_J = 25^\circ C$ unless otherwise specified)	Characteristic Values		
		Min.	Typ.	Max.
BV_{DSS}	$V_{GS} = 0V$, $I_D = 250\mu A$	100		V
$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = 250\mu A$	2.5		V
I_{GSS}	$V_{GS} = \pm 20V$, $V_{DS} = 0V$			± 200 nA
I_{DSS}	$V_{DS} = V_{DSS}$ $V_{GS} = 0V$ $T_J = 150^\circ C$			5 μA
				250 μA
$R_{DS(on)}$	$V_{GS} = 10V$, $I_D = 25A$, Notes 1, 2			9.1 m Ω

Symbol	Test Conditions	Characteristic Values			
		Min.	Typ.	Max.	
$(T_J = 25^\circ\text{C unless otherwise specified})$					
g_{fs}	$V_{DS} = 10\text{V}, I_D = 60\text{A}, \text{Note 1}$	55	93		S
C_{iss}	$V_{GS} = 0\text{V}, V_{DS} = 25\text{V}, f = 1\text{MHz}$		5080		pF
C_{oss}			635		pF
C_{rss}			95		pF
$t_{d(on)}$	Resistive Switching Times $V_{GS} = 10\text{V}, V_{DS} = 0.5 \cdot V_{DSS}, I_D = 25\text{A}$ $R_G = 5\Omega \text{ (External)}$		30		ns
t_r			47		ns
$t_{d(off)}$			44		ns
t_f			28		ns
$Q_{g(on)}$	$V_{GS} = 10\text{V}, V_{DS} = 0.5 \cdot V_{DSS}, I_D = 25\text{A}$		104		nC
Q_{gs}			30		nC
Q_{gd}			29		nC
R_{thJC}	TO-220			0.42	$^\circ\text{C/W}$
R_{thCH}			0.50		$^\circ\text{C/W}$

Source-Drain Diode

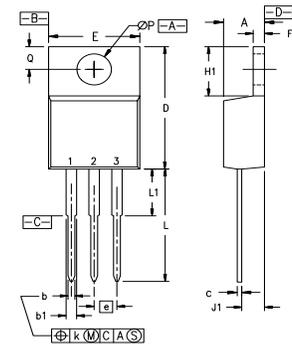
Symbol	Test Conditions	Characteristic Values			
		Min.	Typ.	Max.	
$T_J = 25^\circ\text{C unless otherwise specified}$					
I_S	$V_{GS} = 0\text{V}$			130	A
I_{SM}	Pulse width limited by T_{JM}			350	A
V_{SD}	$I_F = 25\text{A}, V_{GS} = 0\text{V}, \text{Note 1}$			1.0	V
t_{rr}	$I_F = 0.5 \cdot I_S, -di/dt = 100\text{A}/\mu\text{s}$ $V_R = 0.5 \cdot V_{DSS}, V_{GS} = 0\text{V}$		67		ns
I_{RM}			4.7		A
Q_{rr}			160		nC

- Notes: 1. Pulse test, $t \leq 300 \mu\text{s}$; duty cycle, $d \leq 2\%$.
 2. On through-hole packages, $R_{DS(on)}$ Kelvin test contact location must be 5 mm or less from the package body.

TO-263 (IXTA) Outline


Pins: 1 - Gate 2 - Drain
 3 - Source 4, TAB - Drain

Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	4.06	4.83	.160	.190
A1	2.03	2.79	.080	.110
b	0.51	0.99	.020	.039
b2	1.14	1.40	.045	.055
c	0.46	0.74	.018	.029
c2	1.14	1.40	.045	.055
D	8.64	9.65	.340	.380
D1	7.11	8.13	.280	.320
E	9.65	10.29	.380	.405
E1	6.86	8.13	.270	.320
e	2.54	BSC	.100	BSC
L	14.61	15.88	.575	.625
L1	2.29	2.79	.090	.110
L2	1.02	1.40	.040	.055
L3	1.27	1.78	.050	.070
L4	0	0.38	0	.015
R	0.46	0.74	.018	.029

TO-220 (IXTP) Outline


Pins: 1 - Gate 2 - Drain
 3 - Source 4, TAB - Drain

SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.170	.190	4.32	4.83
b	.025	.040	0.64	1.02
b1	.045	.065	1.15	1.65
c	.014	.022	0.35	0.56
D	.580	.630	14.73	16.00
E	.390	.420	9.91	10.66
e	.100 BSC		2.54 BSC	
F	.045	.055	1.14	1.40
H1	.230	.270	5.85	6.85
J1	.090	.110	2.29	2.79
k	0	.015	0	0.38
L	.500	.550	12.70	13.97
L1	.110	.230	2.79	5.84
ØP	.139	.161	3.53	4.08
Q	.100	.125	2.54	3.18

IXYS reserves the right to change limits, test conditions, and dimensions.

IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents:	4,835,592	4,931,844	5,049,961	5,237,481	6,162,665	6,404,065 B1	6,683,344	6,727,585	7,005,734 B2	7,157,338B2
	4,850,072	5,017,508	5,063,307	5,381,025	6,259,123 B1	6,534,343	6,710,405 B2	6,759,692	7,063,975 B2	
	4,881,106	5,034,796	5,187,117	5,486,715	6,306,728 B1	6,583,505	6,710,463	6,771,478 B2	7,071,537	

Fig. 1. Output Characteristics @ 25°C

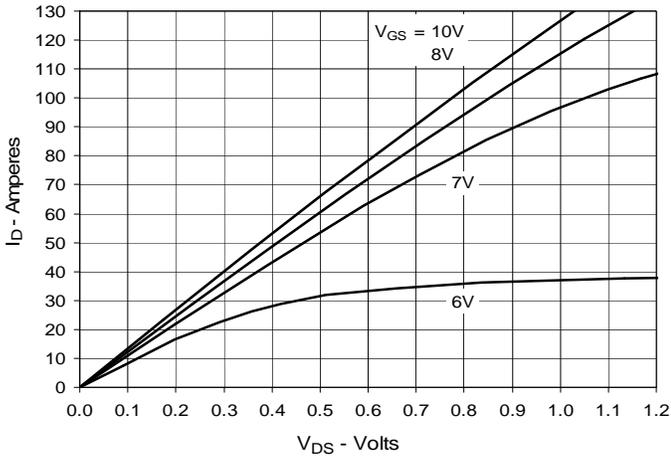


Fig. 2. Extended Output Characteristics @ 25°C

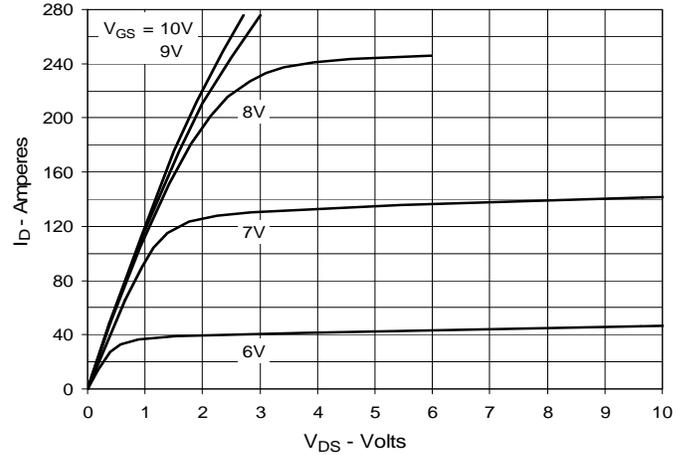


Fig. 3. Output Characteristics @ 150°C

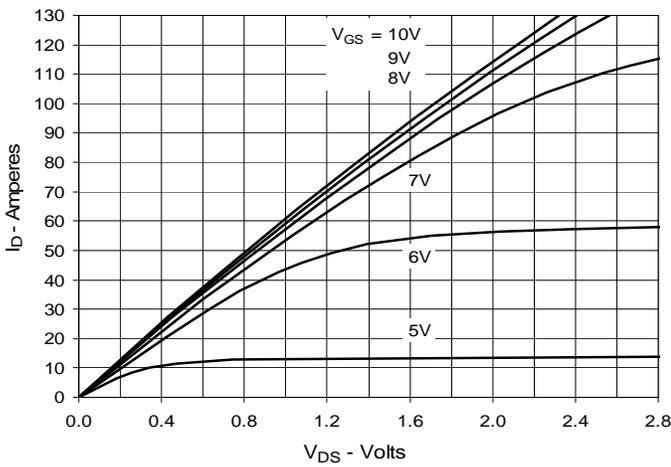


Fig. 4. $R_{DS(on)}$ Normalized to $I_D = 65A$ Value vs. Junction Temperature

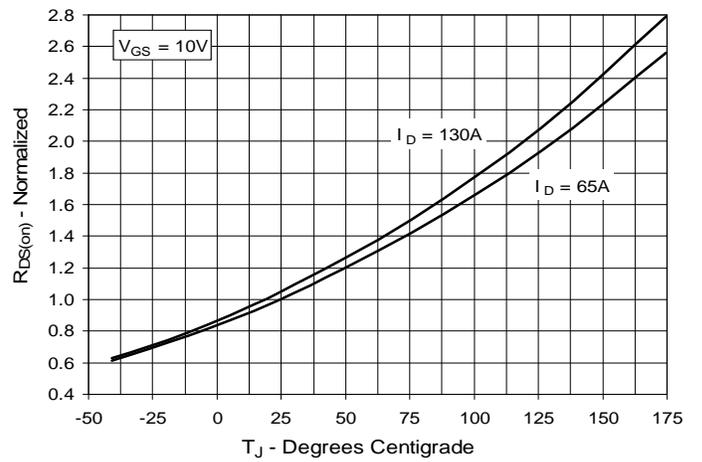


Fig. 5. $R_{DS(on)}$ Normalized to $I_D = 65A$ Value vs. Drain Current

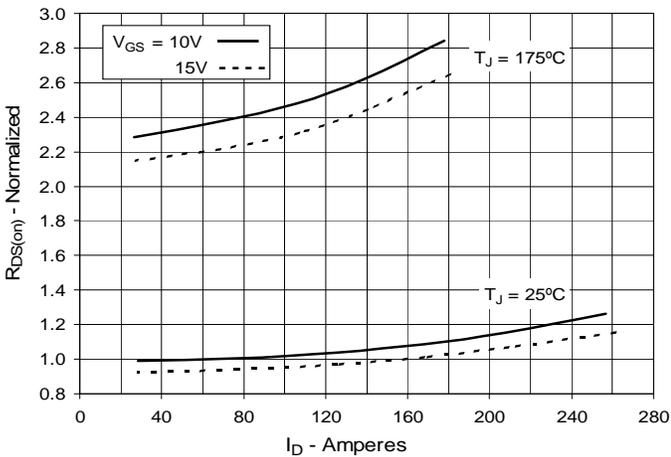


Fig. 6. Drain Current vs. Case Temperature

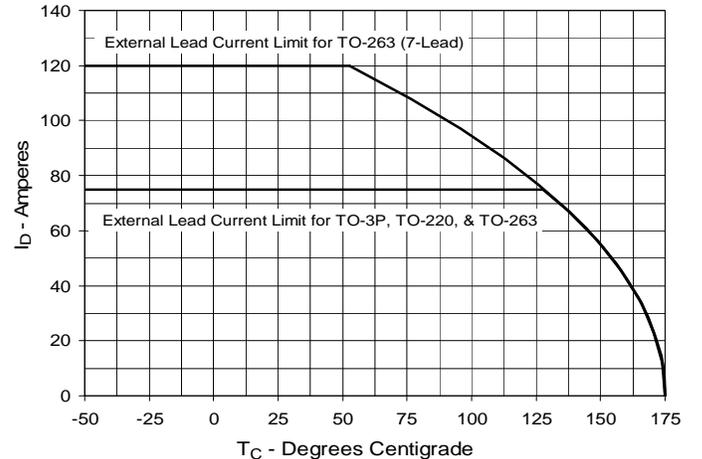


Fig. 7. Input Admittance

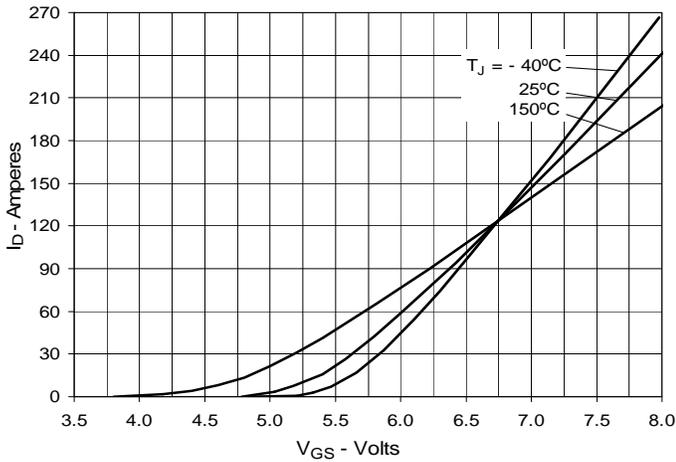


Fig. 8. Transconductance

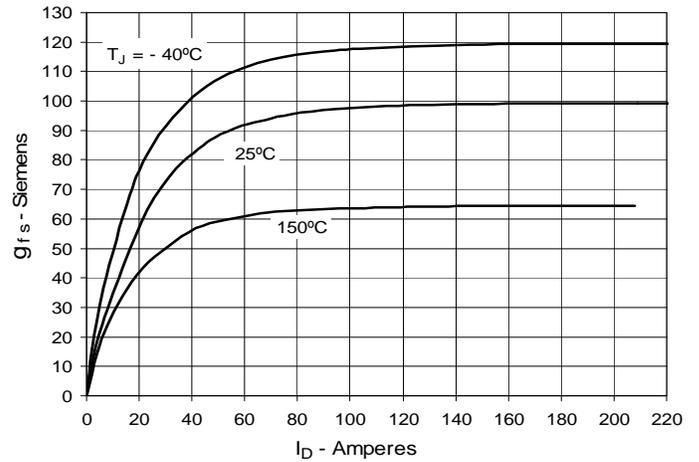


Fig. 9. Forward Voltage Drop of Intrinsic Diode

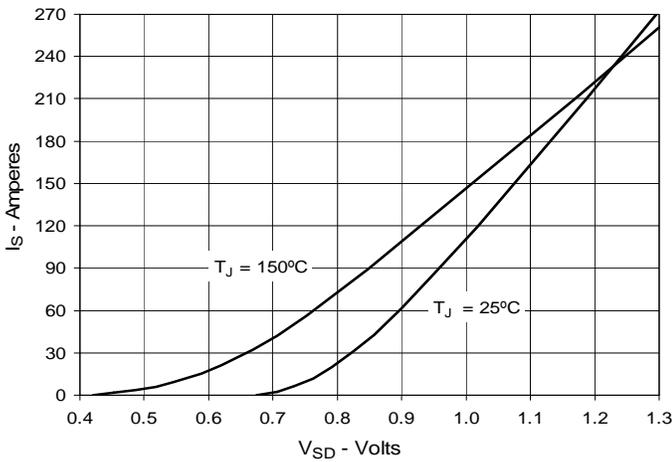


Fig. 10. Gate Charge

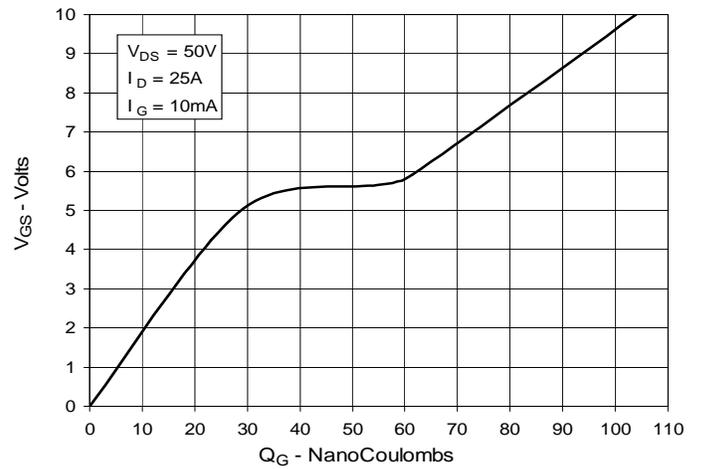


Fig. 11. Capacitance

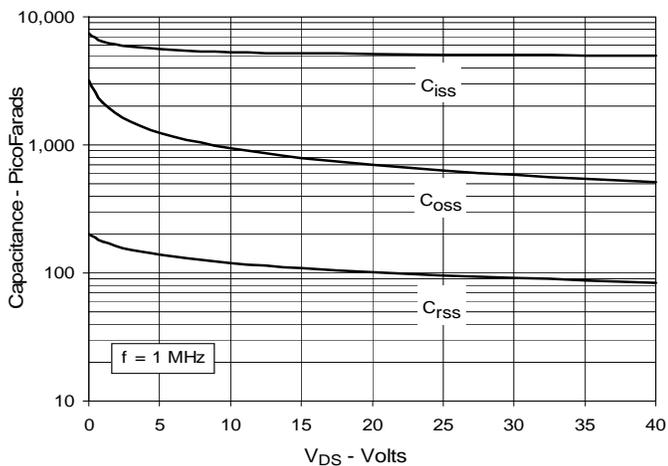


Fig. 12. Maximum Transient Thermal Impedance

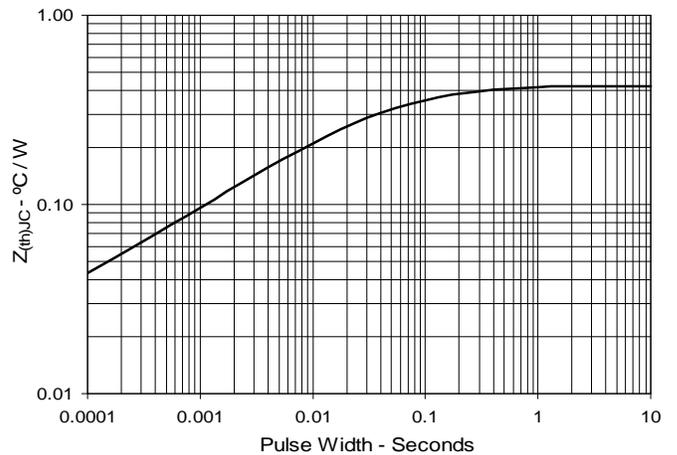


Fig. 13. Resistive Turn-on Rise Time vs. Junction Temperature

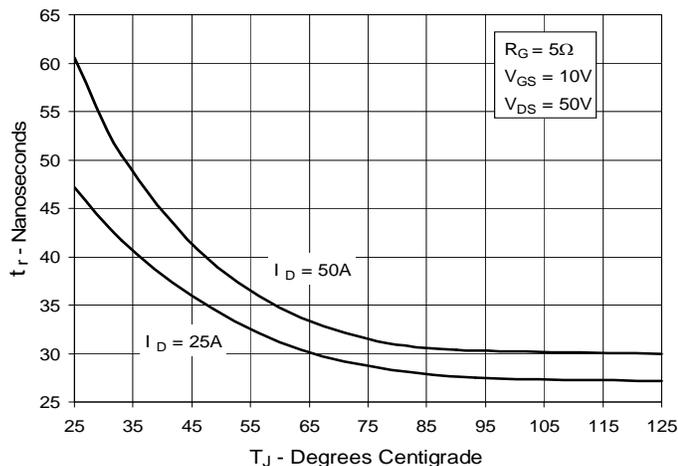


Fig. 14. Resistive Turn-on Rise Time vs. Drain Current

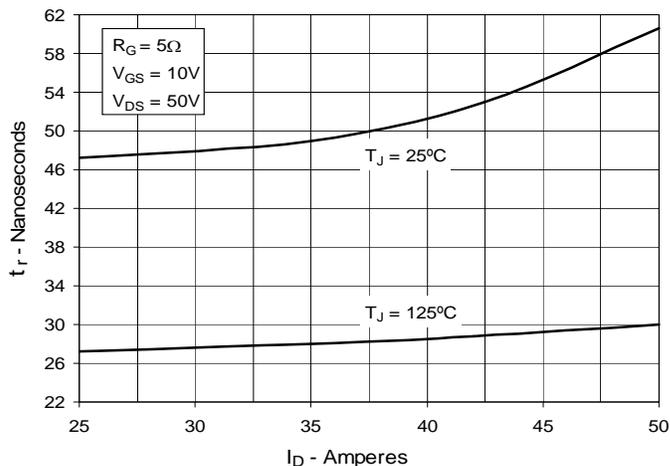


Fig. 15. Resistive Turn-on Switching Times vs. Gate Resistance

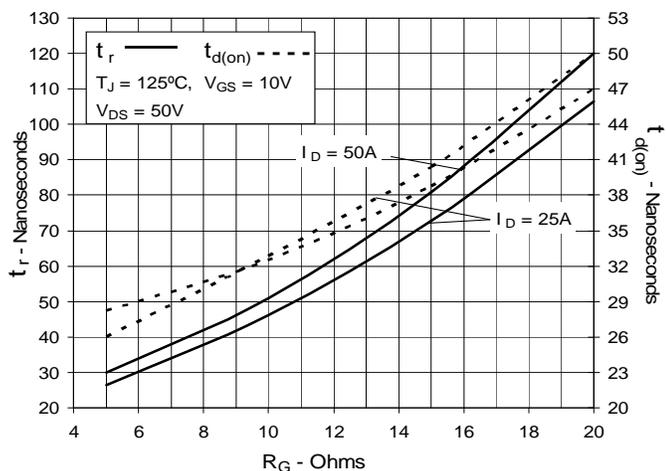


Fig. 16. Resistive Turn-off Switching Times vs. Junction Temperature

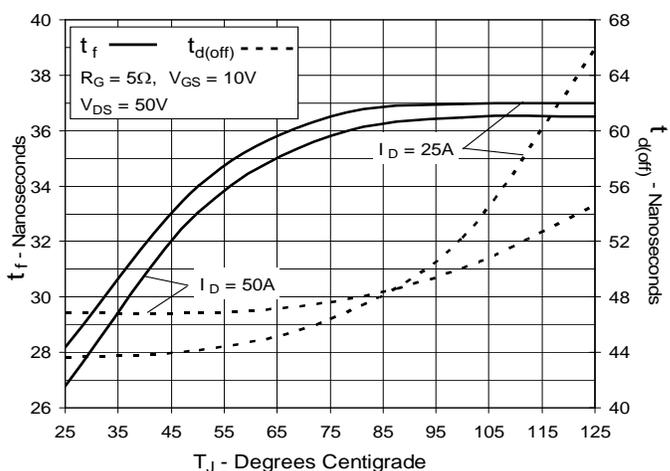


Fig. 17. Resistive Turn-off Switching Times vs. Drain Current

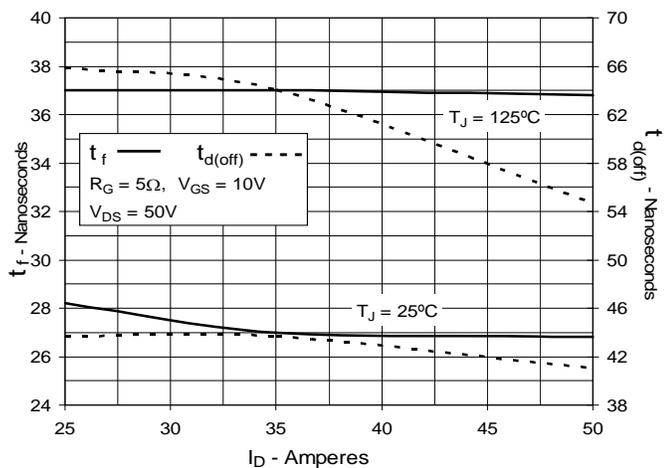


Fig. 18. Resistive Turn-off Switching Times vs. Gate Resistance

